

P-Channel POWER MOSFET

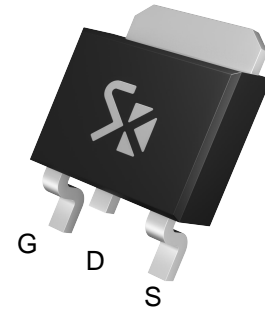
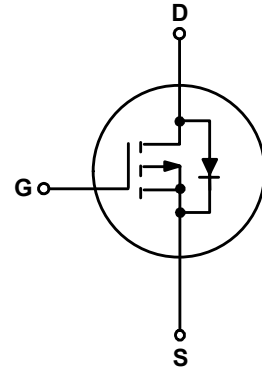
Feature

- -100V P-Channel MOSFET
- $R_{DS(ON)} = 225\text{ m}\Omega @ V_{GS} = -10\text{ V}$
- $R_{DS(ON)} = 250\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
- Advanced trench cell design
- High speed switch

Applications

- Portable appliances
- Battery management

Graphic Symbol



TO-252

1. Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

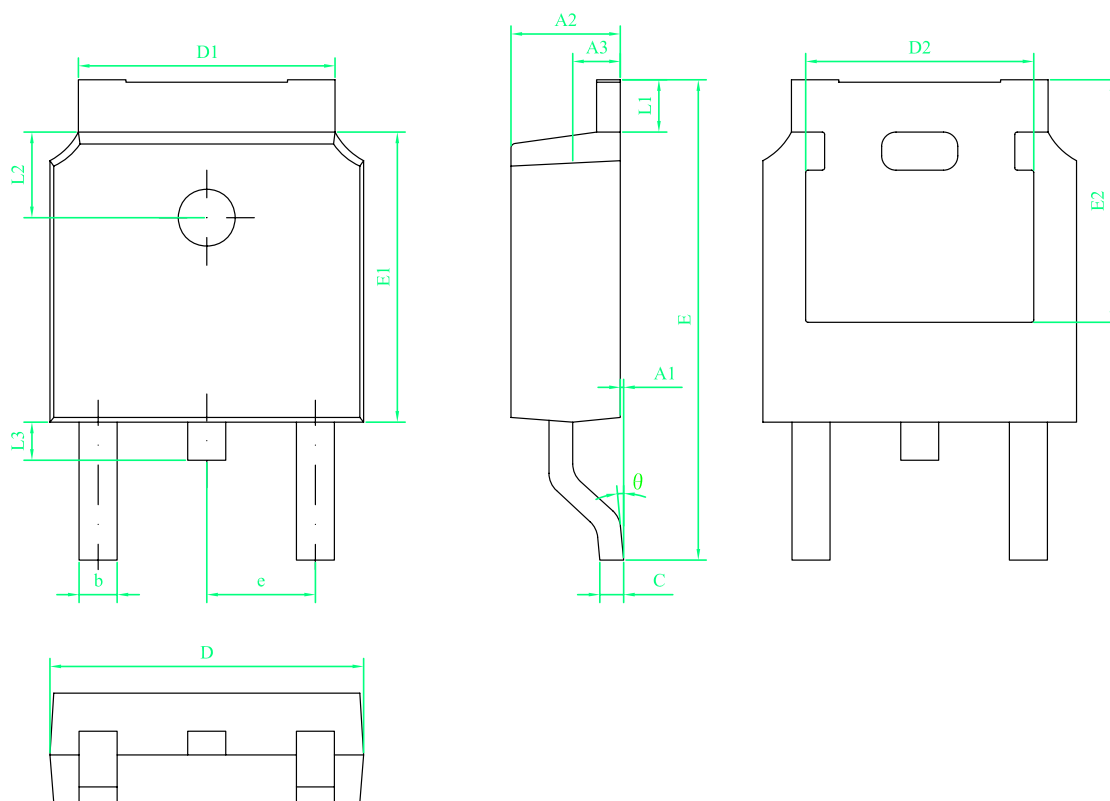
Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-100	V
V_{GSS}	Gate-Source Voltage	± 20	
I_D	Continue Drain Current	-5	A

2. Static Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Condition	SK50P04			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-80V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-30	
V_{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.1	-1.5	-2.3	V
I_{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R_{DS(ON)}	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-0.5A	-	147	225	mΩ
		V _{GS} =-4.5V, I _{DS} =-0.5A	-	159	250	
V_{SD}	Diode Forward Voltage	I _{SD} =-0.5A, V _{GS} =0V	-	-0.75	-1.3	V

PACKAGE OUTLINE

TO-252 PACKAGE OUTLINE DIMENSIONS



符号	尺寸	
	Min	Max
A1	0.00	0.13
A2	2.18	2.39
A3	0.90	1.10
b	0.65	0.85
c	0.46	0.61
D	6.35	6.73
D1	4.95	5.46
D2	4.32	
E	9.40	10.41
E1	5.97	6.22
E2	5.21	
e	2.286 BSC	
L1	0.89	1.27
L2	1.70	1.90
L3	0.60	1.00
θ	0.00	8.00